SILICON PNP-DARLINGTON POWER TRANSISTOR

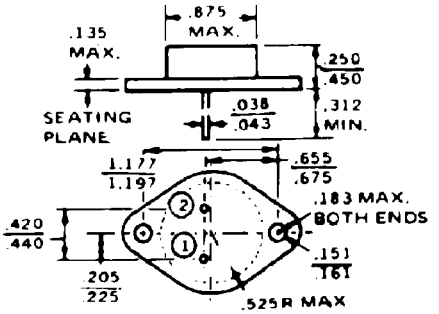
DESCRIPTION:

The **2N6054** is Designed for General Purpose Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	8.0 A
V_{CE}	-80 V
P_{DISS}	100 W @ T_C = 25 °C
T_J	65 °C to +200 °C
T_{STG}	65 °C to +200 °C
θ_{JC}	1.75 °C/W

PACKAGE STYLE TO-3



Lead 1=Base, Lead 2=Emitter, Case=Collector

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 100 mA			-80			V
I_{CEO}	V_{CE} = -40 V					0.5	mA
I_{CEX}	V_{CE} = -80 V	$V_{BE\ (off)}$ = 1.5 V				0.5	mA
			T_C = 150 °C			5.0	
I_{EBO}	V_{EB} = -5.0 V					2.0	mA
h_{FE}	V_{CE} = -3.0 V	I_C = 4.0 A		750		18000	---
$V_{CE(SAT)}$	I_C = 4.0 A	I_B = 16 mA				-2.0	V
	I_C = 8.0 A	I_B = 80 mA				-3.0	
$V_{BE(on)}$	V_{CE} = -3.0 V	I_C = 4.0 A				-2.8	V
$V_{BE(SAT)}$	I_C = 8.0 A	I_B = 80 mA				-4.0	V
h_{fe}	V_{CE} = -3.0 V	I_C = 3.0 A	f = 1.0 KHz	300			---
f_t	V_{CE} = -3.0 V	I_C = 3.0 A	f = 1.0 MHz	4.0			---
C_{ob}	V_{CB} = -10 V		f = 100 KHz			300	pF